论文

Pt-GaAs肖特基势垒雪崩光电探测器的研究

郭康瑾, 胡维央, 姚文兰, 陈莲勇

中国科学院上海冶金研究所 上海 200233

收稿日期 1991-6-16 修回日期 1991-11-26 网络版发布日期 2009-9-4 接受日期

Pt-GaAs 肖特基势垒雪崩光电探测器已研制成功。器件制作在施主浓度为 $0.5 \sim 3 \times 10^{15} cm^{-3}$ 、厚度约为 $20 \mu m$ 的GaAs外延层上。为防止边缘击穿,用能量为500keV、剂量为 1×10^{15} cm $^{-2}$ 的质子轰击,在直径为150μm的光 敏区外形成高阻保护区。半透明的Pt肖特基势垒膜用特殊的蒸发法形成。器件的峰值响应波长随偏压的改 变可以从8600 (Å) 移动到8835 (Å), 截止波长可延伸到9700 (Å), 观察到明显的Franz-Ke1dysh效应。器件倍增 可达100以上;暗电流仅几纳安;过剩噪声系数为7;上升、下降时间短于1ns。这种器件可与FET实现平面集

关键词 雪崩光电探测器 GaAs 肖特基势垒

分类号

STUDY ON Pt-GaAs SCHOTTKY BARRIER APD

Guo Kangjin, Hu Weiyang, Yao Wenlan, Chen Lianyong

Shanghai Institute of Metallurgy Academia Sinica Shanghai 200233

Abstract

Pt-GaAs Schottky barrier APDs have been investigated. The devices were fabricated on GaAs epitaxial layer with carrier concentration of 0.5-3×10¹⁵cm⁻³ and thickness of about 20 µm. Guard ring along with sensitive area was formed by H+ bombardment with energy of 500 keV and dosage of 1×10¹⁵cm⁻² to prevent edge breakdown. Semitransparem Pt film was evaporated using a special evaporation source. The peak response wavelength of the device is 8600Å -8835Å at different bias voltages. Optical absopdon edge could extended to 9700Å. Franz-Keldysh effect has been observed. The multiplication of above 100 could reach. Dark current is about several nA. Excess noise coefficient is 7 and both rise and fall time were less than 1 ns. The device could be integrated monolithically and planarly with GaAs FET.

Key words Avalanche photo-detector GaAs Schottky barrier

通讯作者

DOI:

作者个人主

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郭康瑾: 胡维央: 姚文兰: 陈莲勇

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· 郭康瑾

胡维央

・姚文兰

· 陈莲勇